Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	235	tokyo.asn. and electron.asn. and (heat near4 chamber) and heater	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:49
L2	2	tokyo.asn. and electron.asn. and (recirculating) and (coating near10 solution)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:51
L3	1	tokyo.asn. and electron.asn. and (recirculation) and (coating near10 solution)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:51
L4	6	tokyo.asn. and electron.asn. and (recycling) and (coating near10 solution)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:51
L5	6	(("5168887") or ("5235995") or ("5431421") or ("5658387") or ("6066575") or ("6375741")).PN.	USPAT	OR	OFF	2004/11/15 11:54
L6	0	5 and (recircul)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:59
L7	2	5 and (recircul$)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:54
L8	4	5 and framework	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:59

L9	5	5 and (processor near3 head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 12:00
L10	5	5 and ("250")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 12:15
L11	0	5 and (dissipator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 12:16
L12	0	5 and (dissipater)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 12:16
L13	0	5 and ((heat near4 source) same platform)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 12:16
L14	1	5 and ((heat near4 chamber))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 12:16

S1	49	US-3641973-$.DID. OR US-3770598-$.DID. OR US-3798056-$.DID. OR US-3950184-$.DID. OR US-3962047-$.DID. OR US-3978578-$.DID. OR US-4027686-$.DID. OR US-4092176-$.DID. OR US-4110176-$.DID. OR US-4113492-$.DID. OR US-4118303-$.DID. OR US-4137867-$.DID. OR US-4170959-$.DID. OR US-4226208-$.DID. OR US-4246088-$.DID. OR US-4259166-$.DID. OR US-4280882-$.DID. OR US-4304641-$.DID. OR US-4315059-$.DID. OR US-4336114-$.DID. OR US-4339313-$.DID. OR US-4339319-$.DID. OR US-4341613-$.DID. OR US-4351266-$.DID. OR US-4373988-$.DID.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 20:49
S2	25	US-3641973-$.DID. OR US-3770598-$.DID. OR US-3798056-$.DID. OR US-3950184-$.DID. OR US-3962047-$.DID. OR US-3978578-$.DID. OR US-4027686-$.DID. OR US-4092176-$.DID. OR US-4110176-$.DID. OR US-4113492-$.DID. OR US-4118303-$.DID. OR US-4137867-$.DID. OR US-4170959-$.DID. OR US-4226208-$.DID. OR US-4246088-$.DID. OR US-4259166-$.DID. OR US-4280882-$.DID. OR US-4304641-$.DID. OR US-4315059-$.DID. OR US-4336114-$.DID. OR US-4339313-$.DID. OR US-4339319-$.DID. OR US-4341613-$.DID. OR US-4351266-$.DID. OR US-4373988-$.DID.	USPAT; USOCR	OR	ON	2004/11/14 21:07

S3	27	US-4376685-$.DID. OR US-4405416-$.DID. OR US-4428815-$.DID. OR US-4435266-$.DID. OR US-4466864-$.DID. OR US-4469566-$.DID. OR US-4489740-$.DID. OR US-4510176-$.DID. OR US-4514266-$.DID. OR US-4518678-$.DID. OR US-4534832-$.DID. OR US-4565607-$.DID. OR US-4597836-$.DID. OR US-4624749-$.DID. OR US-4675096-$.DID. OR US-4693805-$.DID. OR US-4696729-$.DID. OR US-4732785-$.DID. OR US-4750505-$.DID. OR US-4827867-$.DID. OR US-4828654-$.DID. OR US-4838978-$.DID. OR US-4838979-$.DID. OR US-4856456-$.DID. OR US-4856641-$.DID. OR US-4861452-$.DID. OR US-4861563-$.DID.	USPAT; USOCR	OR	ON	2004/11/14 21:37
S4	27	US-4879007-$.DID. OR US-4906346-$.DID. OR US-4924890-$.DID. OR US-4931149-$.DID. OR US-5000827-$.DID. OR US-5024746-$.DID. OR US-5039381-$.DID. OR US-5055425-$.DID. OR US-5069760-$.DID. OR US-5078852-$.DID. OR US-5092975-$.DID. OR US-5096550-$.DID. OR US-5100502-$.DID. OR US-5100516-$.DID. OR US-5155336-$.DID. OR US-5158100-$.DID. OR US-5162260-$.DID. OR US-5169408-$.DID. OR US-5222310-$.DID. OR US-5224504-$.DID. OR US-5227041-$.DID. OR US-5228966-$.DID. OR US-5230743-$.DID. OR US-5238500-$.DID. OR US-5252807-$.DID. OR US-5256274-$.DID. OR US-5259407-$.DID.	USPAT; USOCR	OR	ON	2004/11/14 21:14

S5	21	US-5275976-$.DID. OR US-5290361-$.DID. OR US-5294257-$.DID. OR US-5312487-$.DID. OR US-5316974-$.DID. OR US-5328589-$.DID. OR US-5232328-$.DID. OR US-5332487-$.DID. OR US-5235995-$.DID. OR US-5252137-$.DID. OR US-5270248-$.DID. OR US-5340437-$.DID. OR US-5349978-$.DID. OR US-5368711-$.DID. OR US-5372699-$.DID. OR US-5377708-$.DID. OR US-5391285-$.DID. OR US-5405518-$.DID. OR US-5415890-$.DID. OR US-5421987-$.DID. OR US-5429733-$.DID.	USPAT; USOCR	OR	ON	2004/11/14 21:14
S6	2	("4651640").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 21:38
S7	2	("4651440").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:08
S8	2	("5156174").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:49
S9	2	("4590094").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/15 09:19
S10	10	("3136323" | "3494815" | "4027686" | "4161356" | "4745422" | "4788994" | "4871417" | "4922277").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:28
S11	109	"118"/$.ccls. and polyvinylidene and fluoride	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:29

S12	90	"118"/$.ccls. and (polyvinylidene near2 fluoride)	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:29
S13	1	"118"/$.ccls. and (polyvinylidene near2 fluoride) and (acid near3 resistant)	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:51
S14	9	"118"/$.ccls. and (polyvinylidene near2 fluoride) and (wafer near3 holder)	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:29
S15	0	"118"/$.ccls. and (polyvinylidene near2 fluoride) and (wafer near3 chuck)	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:30
S16	1	"118"/$.ccls. and (polyvinylidene near2 fluoride) and (semiconductor same chuck)	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:31
S17	10	"118"/$.ccls. and (polyvinylidene near2 fluoride) and (semiconductor same holder)	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:31
S18	6	(("5168887") or ("5235995") or ("5431421") or ("5658387") or ("6066575") or ("6375741")).PN.	USPAT	OR	OFF	2004/11/14 22:50
S19	44	semitool and polyvinylidene	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 22:51
S20	41	semitool.asn. and (polyvinylidene near2 fluoride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 22:51
S21	12	(semiconductor or wafer) and (process$5 near10 chamber) and (polyvinylidene near2 fluoride) and (acid near3 resistant)	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 23:49
S22	1409	(118/52).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:51
S24	799	(118/302).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:52

S25	1656	(118/323).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:52
S26	88	(118/21).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:52
S27	143	(118/683).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:53
S28	287	(118/667).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:53
S29	1171	(118/300).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:53
S30	525	(118/313).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:53
S31	861	(118/315).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 22:53
S32	944	(118/320).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:28
S33	0	(semiconductor or wafer) and (process$5 near10 chamber) and (polyvinylidene near2 fluoride) and (acid near3 retardant)	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 22:56

S34	1395	(427/240).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:29
S35	2456	(427/372.2).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:29
S36	811	(427/421).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:29
S37	0	(427/423).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:29
S38	567	(427/425).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:29
S39	152	(427/72).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:29
S40	1599	(427/96).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:29
S41	241	(438/760).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:29

S42	766	(438/758).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:30
S44	510	(438/782).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:30
S45	766	(134/33).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:30
S46	351	(134/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:30
S47	1115	(134/153).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:30
S48	638	(134/157).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:31
S49	2240	(134/902).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:31
S50	697	(134/182).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:31

S51	1050	(134/200).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:31
S52	429	(134/183).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/14 23:31
S53	9	(semiconductor or wafer) and ((process$5 near10 chamber) same (acid near3 resistant))	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/14 23:51
S54	2	(("4222345") or ("4282825")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/15 11:26